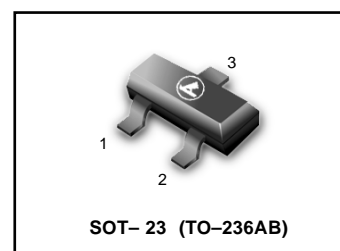


# General Purpose Transistors

## PNP Silicon

- We declare that the material of product compliance with RoHS requirements.
- S - Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

**LMBT4403LT1G**  
**S-LMBT4403LT1G**



### ORDERING INFORMATION

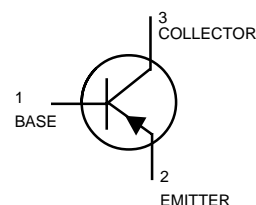
Device	Marking	Shipping
LMBT4403LT1G S-LMBT4403LT1G	2T	3000/Tape & Reel
LMBT4403LT3G S-LMBT4403LT3	2T	10000/Tape & Reel

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CE0}$	- 40	Vdc
Collector–Base Voltage	$V_{CBO}$	- 40	Vdc
Emitter–Base Voltage	$V_{EBO}$	- 5.0	Vdc
Collector Current — Continuous	$I_C$	- 600	mAdc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR -5 Board (1) $T_A = 25^\circ\text{C}$	$P_D$	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (2) $T_A = 25^\circ\text{C}$	$P_D$	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	°C



### DEVICE MARKING

LMBT4403LT1G = 2T

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (3) ( $I_C = -1.0\text{ mAdc}, I_B = 0$ )	$V_{(BR)CEO}$	- 40	—	Vdc
Collector–Base Breakdown Voltage ( $I_C = -0.1\text{ mAdc}, I_E = 0$ )	$V_{(BR)CBO}$	- 40	—	Vdc
Emitter–Base Breakdown Voltage ( $I_E = -0.1\text{ mAdc}, I_C = 0$ )	$V_{(BR)EBO}$	- 5.0	—	Vdc
Base Cutoff Current ( $V_{CE} = -35\text{ Vdc}, V_{EB} = -0.4\text{ Vdc}$ )	$I_{BEV}$	—	- 0.1	$\mu\text{Adc}$
Collector Cutoff Current ( $V_{CE} = -35\text{ Vdc}, V_{EB} = -0.4\text{ Vdc}$ )	$I_{CEX}$	—	- 0.1	$\mu\text{Adc}$

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

3. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ ; Duty Cycle  $\leq 2.0\%$ .

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ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
<b>ON CHARACTERISTICS</b>				
DC Current Gain (I <sub>C</sub> = -0.1 mAdc, V <sub>CE</sub> = -1.0 Vdc)	h <sub>FE</sub>	30	—	—
(I <sub>C</sub> = -1.0 mAdc, V <sub>CE</sub> = -1.0 Vdc)		60	—	
(I <sub>C</sub> = -10 mAdc, V <sub>CE</sub> = -1.0 Vdc)		100	—	
(I <sub>C</sub> = -150 mAdc, V <sub>CE</sub> = -2.0 Vdc)(3)		100	300	
(I <sub>C</sub> = -500 mAdc, V <sub>CE</sub> = -2.0 Vdc)(3)		20	—	
Collector-Emitter Saturation Voltage(3) (I <sub>C</sub> = -150mAdc, I <sub>B</sub> = -15 mAdc)	V <sub>CE(sat)</sub>	—	- 0.4	Vdc
(I <sub>C</sub> = -500 mAdc, I <sub>B</sub> = -50 mAdc)		—	- 0.75	
Base-Emitter Saturation Voltage (3) (I <sub>C</sub> = -150 mAdc, I <sub>B</sub> = -15 mAdc)	V <sub>BE(sat)</sub>	- 0.75	- 0.95	Vdc
(I <sub>C</sub> = -500 mAdc, I <sub>B</sub> = -50 mAdc)		—	- 1.3	

SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product (I <sub>C</sub> = -20mAdc, V <sub>CE</sub> = -10 Vdc, f = 100 MHz)	f <sub>T</sub>	200	—	MHz
Collector-Base Capacitance (V <sub>CB</sub> = -10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>cb</sub>	—	8.5	pF
Emitter-Base Capacitance (V <sub>BE</sub> = -0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>eb</sub>	—	30	pF
Input Impedance (V <sub>CE</sub> = -10 Vdc, I <sub>C</sub> = -1.0 mAdc, f = 1.0 kHz)	h <sub>ie</sub>	1.5	15	kΩ
Voltage Feedback Ratio (V <sub>CE</sub> = -10 Vdc, I <sub>C</sub> = -1.0 mAdc, f = 1.0 kHz)	h <sub>re</sub>	0.1	8.0	X 10 <sup>-4</sup>
Small-Signal Current Gain (V <sub>CE</sub> = -10 Vdc, I <sub>C</sub> = -1.0 mAdc, f = 1.0 kHz)	h <sub>fe</sub>	60	500	—
Output Admittance (V <sub>CE</sub> = -10 Vdc, I <sub>C</sub> = -1.0 mAdc, f = 1.0 kHz)	h <sub>oe</sub>	1.0	100	μmhos

SWITCHING CHARACTERISTICS

Delay Time	(V <sub>CC</sub> = -30 Vdc, V <sub>EB</sub> = -2.0 Vdc,	t <sub>d</sub>	—	15	ns
Rise Time	I <sub>C</sub> = -150mAdc, I <sub>B1</sub> = -15 mAdc)	t <sub>d</sub>	—	20	
Storage Time	(V <sub>CC</sub> = -30 Vdc, I <sub>C</sub> = -150 mAdc,	t <sub>s</sub>	—	225	ns
Fall Time	I <sub>B1</sub> = I <sub>B2</sub> = -15 mAdc)	t <sub>f</sub>	—	30	

3. Pulse Test: Pulse Width ≤300 μs; Duty Cycle ≤2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

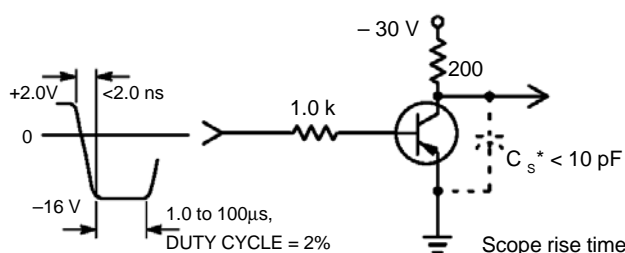


Figure 1. Turn-On Time

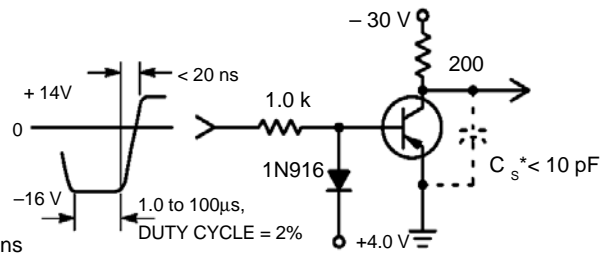


Figure 2. Turn-Off Time

\*Total shunt capacitance of test jig connectors, and oscilloscope

TYPICAL TRANSIENT CHARACTERISTICS

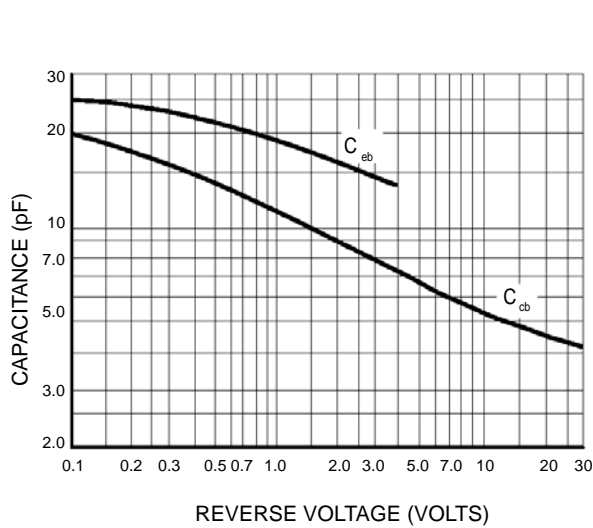


Figure 3. Capacitance

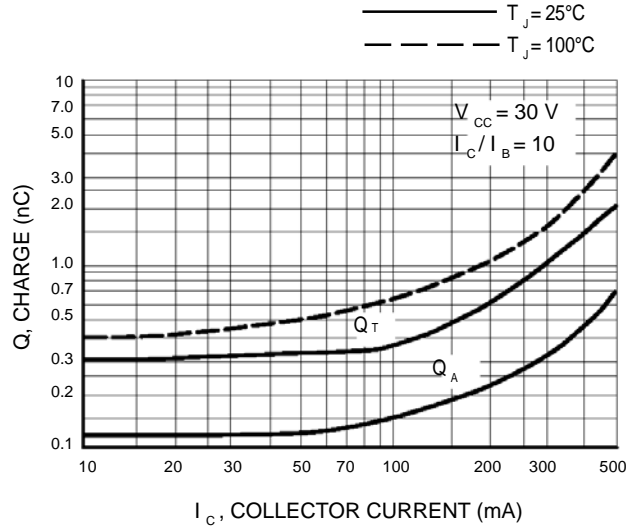


Figure 4. Charge Data

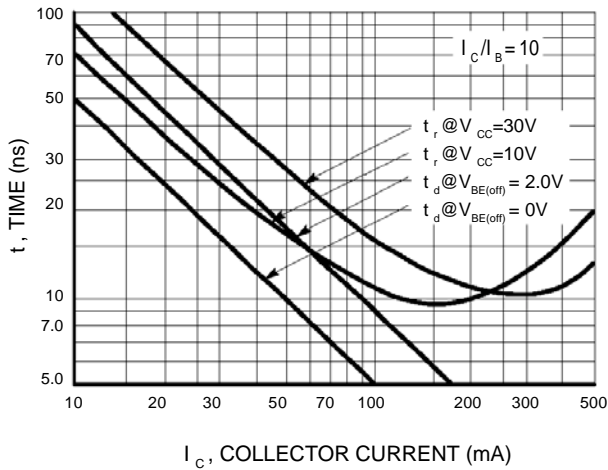


Figure 5. Turn-On Time

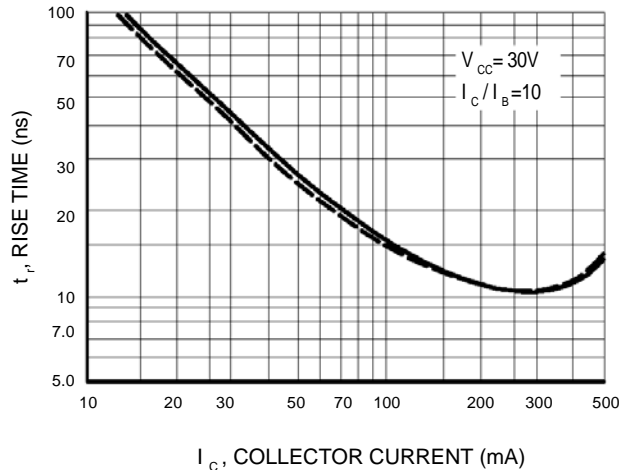


Figure 6. Rise Time

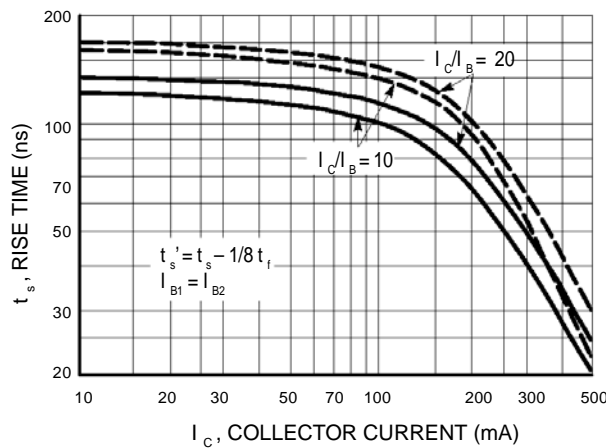


Figure 7. Storage Time

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SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE

$V_{CE} = -10 \text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$   
Bandwidth = 1.0 Hz

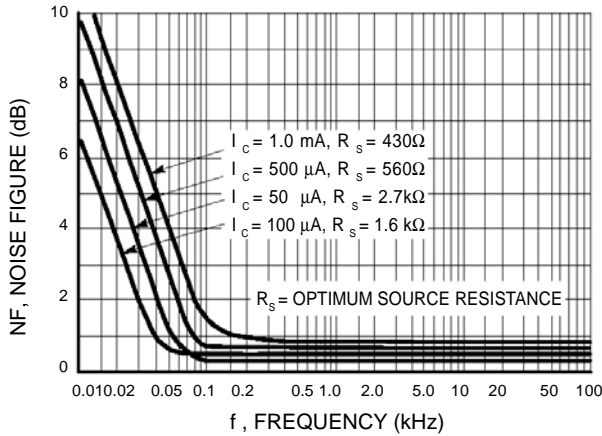


Figure 8. Frequency Effects

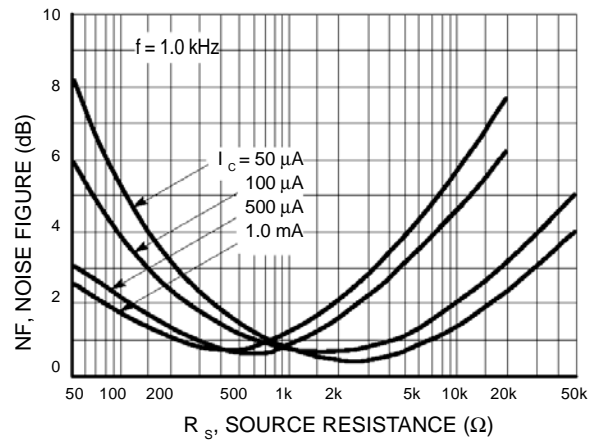


Figure 9. Source Resistance Effects

h PARAMETERS

( $V_{CE} = -10 \text{ Vdc}$ ,  $f = 1.0 \text{ kHz}$ ,  $T_A = 25^\circ\text{C}$ )

This group of graphs illustrates the relationship between  $h_{fe}$  and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were selected from the MMBT4401LT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

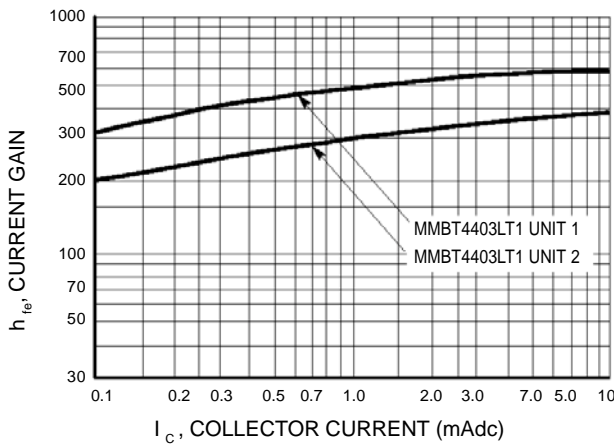


Figure 10. Current Gain

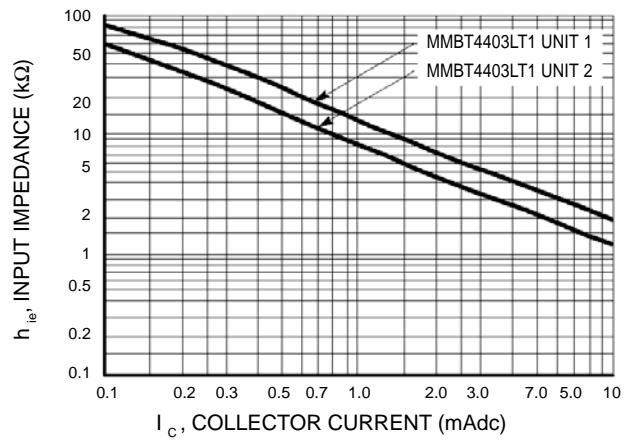


Figure 11. Input Impedance

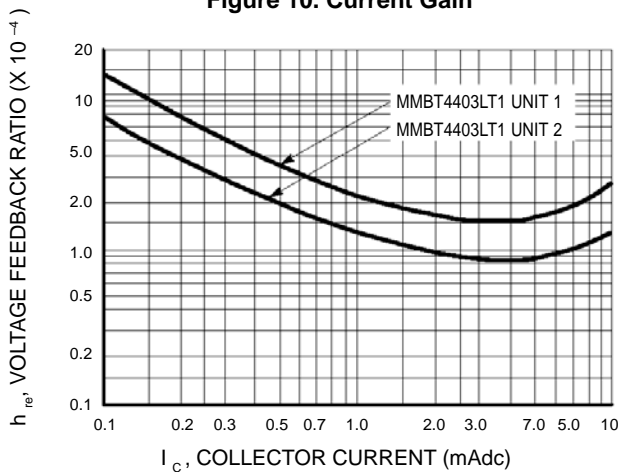


Figure 12. Voltage Feedback Ratio

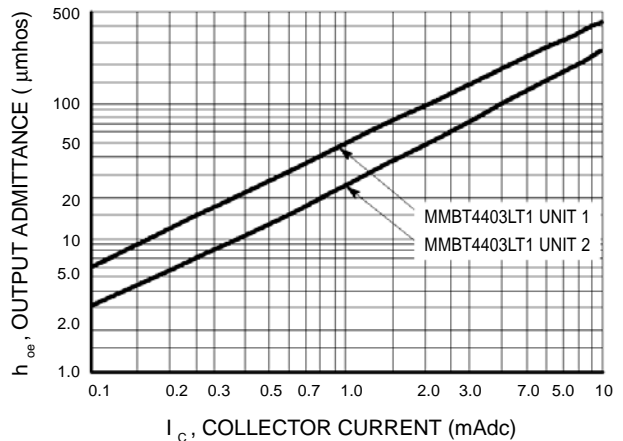


Figure 13. Output Admittance

STATIC CHARACTERISTICS

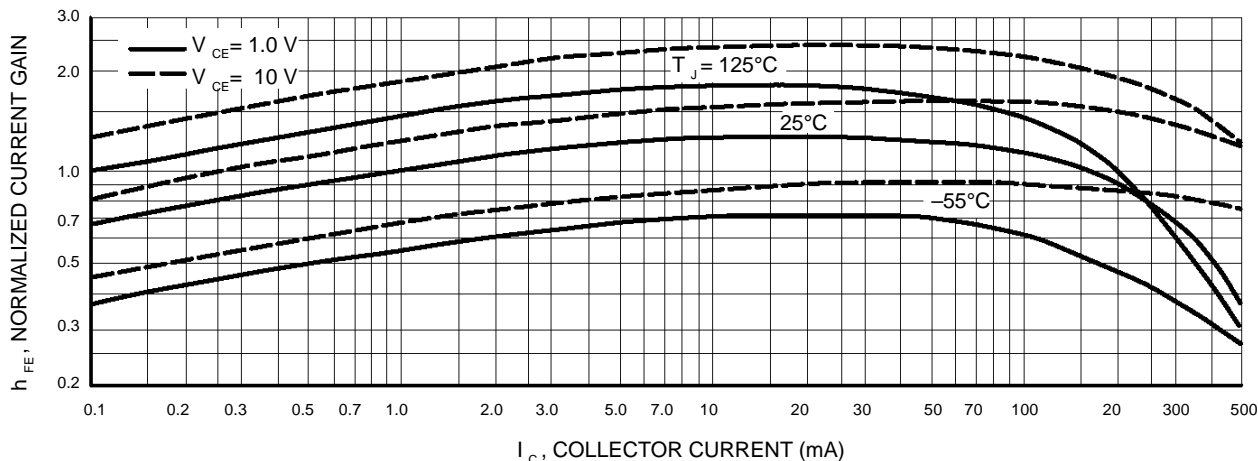


Figure 14. DC Current Gain

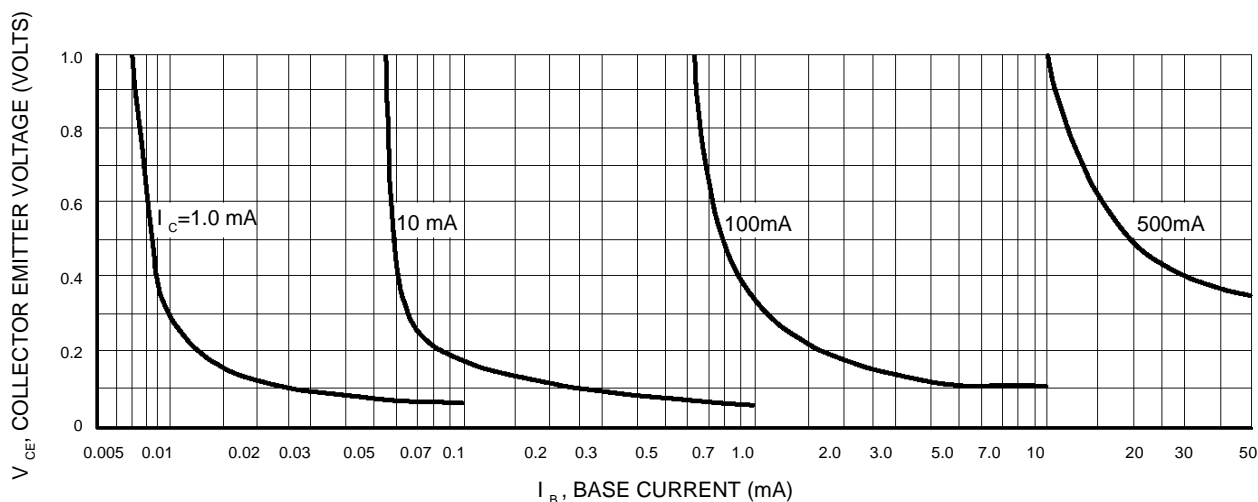


Figure 15. Collector Saturation Region

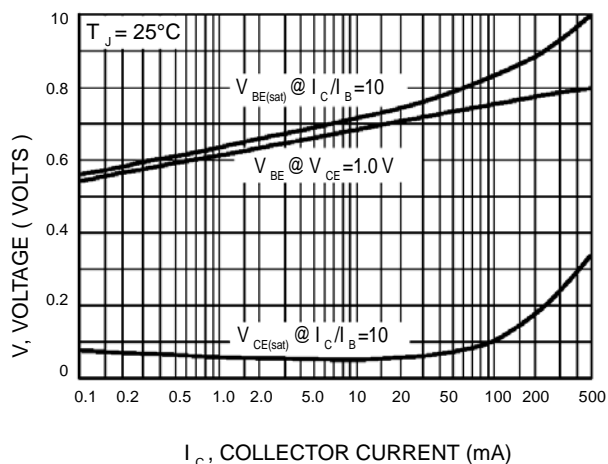


Figure 16. "On" Voltages

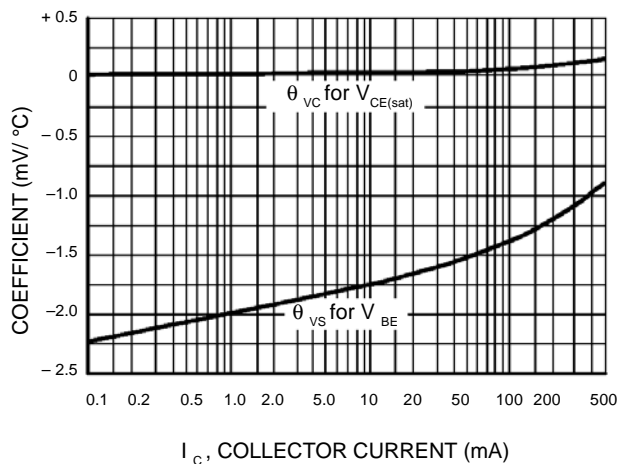
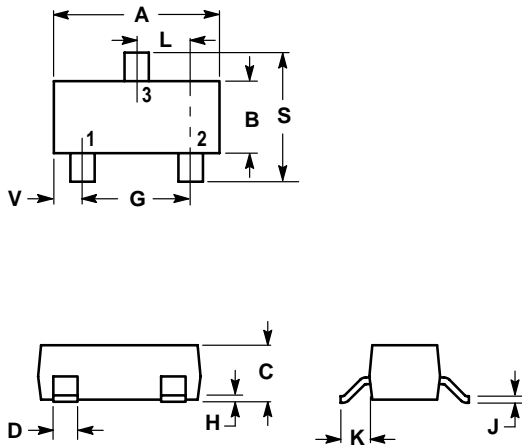


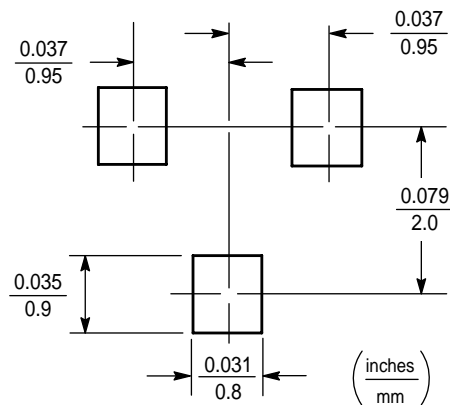
Figure 17. Temperature Coefficients

**SOT-23**
**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60



单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)